## FEATURES

1.8 V to 5.5 V single supply
$4 \Omega$ (max) on resistance
$0.75 \Omega$ (typ) on resistance flatness
$-\mathbf{3 d B}$ bandwidth > 200 MHz
Rail-to-rail operation
6-Lead SOT-23 package and 8-Lead MSOP package
Fast switching times:

$$
\begin{aligned}
& \mathrm{t}_{\mathrm{oN}}=12 \mathrm{~ns} \\
& \text { toff }=6 \mathrm{~ns}
\end{aligned}
$$

Typical power consumption: (<0.01 $\boldsymbol{\mu W}$ )
TTL/CMOS compatible

## APPLICATIONS

## Battery-powered systems

## Communication systems

Sample-and-hold systems
Audio signal routing
Video switching
Mechanical reed relay replacement

## GENERAL DESCRIPTION

The ADG719 is a monolithic CMOS SPDT switch. This switch is designed on a submicron process that provides low power dissipation yet gives high switching speed, low on resistance, and low leakage currents.
The ADG719 can operate from a single-supply range of 1.8 V to 5.5 V , making it ideal for use in battery-powered instruments and with the new generation of DACs and ADCs from Analog Devices, Inc.

Each switch of the ADG719 conducts equally well in both directions when on. The ADG719 exhibits break-before-make switching action.
Because of the advanced submicron process, -3 dB bandwidths of greater than 200 MHz can be achieved.

The ADG719 is available in a 6-lead SOT-23 package and an 8-lead MSOP package.

## FUNCTIONAL BLOCK DIAGRAM



NOTES

1. SWITCHES SHOWN FOR A LOGIC 1 INPUT. 鯯

Figure 1.

## PRODUCT HIGHLIGHTS

1. 1.8 V to 5.5 V Single-Supply Operation. The ADG719 offers high performance, including low on resistance and fast switching times, and is fully specified and guaranteed with 3 V and 5 V supply rails.
2. Very Low Ron ( $4 \Omega$ Max at 5 V and $10 \Omega$ Max at 3 V ). At 1.8 V operation, R $\mathrm{R}_{\mathrm{ON}}$ is typically $40 \Omega$ over the temperature range.
3. Automotive Temperature Range: $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$.
4. On Resistance Flatness ( $\mathrm{R}_{\text {flat(on) }}$ ) ( $0.75 \Omega$ typ).
5. -3 dB Bandwidth $>200 \mathrm{MHz}$.
6. Low Power Dissipation. CMOS construction ensures low power dissipation.
7. Fast $\mathrm{t}_{\mathrm{O}} / \mathrm{t}_{\mathrm{ofF}}$.
8. Tiny, 6-lead SOT-23 and 8-lead MSOP packages.

Rev. D

## ADG719

## TABLE OF CONTENTS

Features ..... 1
Applications .....  1
Functional Block Diagram ..... 1
General Description .....  1
Product Highlights ..... 1
Revision History ..... 2
Specifications ..... 3
Absolute Maximum Ratings ..... 5
ESD Caution ..... 5
Pin Configuration and Function Descriptions ..... 6
REVISION HISTORY
3/10—Rev. C to Rev. D
Removed B Version Text ..... Throughout
Changes to Figure 1 .....  1
Deleted Endnote 1 (Table 1) ..... 3
Deleted Endnote 1 (Table 2) ..... 4
Changes to Figure 2 .....  6
Changes to Ordering Guide ..... 14
12/09—Rev. B to Rev. C
Updated Format Universal
Changes to Table 3 ..... 5
Added Table 4. ..... 6
Changes to Terminology Section. ..... 11
Updated Outline Dimensions ..... 13
Changes to Ordering Guide ..... 14
7/02-Rev. A to Rev. B.
Changes to Product Name .....  1
Changes to Features .....  1
Additions to Product Highlights ..... 1
Changes to Specifications ..... 2
Edits to Absolute Maximum Ratings ..... 4
Changes to Terminology ..... 4
Edits to Ordering Guide ..... 4
Added New TPCs 4 and 5 .....
Replaced TPC 10. ..... 6
Test Circuits 6, 7, and 8 Replaced ..... 7
Updated RM-8 and RT-6 Package Outlines ..... 9
Typical Performance Characteristics ..... 7
Test Circuits .....  9
Terminology ..... 11
Applications Information ..... 12
ADG719 Supply Voltages ..... 12
On Response vs. Frequency ..... 12
Off Isolation ..... 12
Outline Dimensions ..... 13
Ordering Guide ..... 14

## SPECIFICATIONS

$\mathrm{V}_{\mathrm{DD}}=5 \mathrm{~V} \pm 10 \%, \mathrm{GND}=0 \mathrm{~V}$.
Table 1.


[^0]
## ADG719

$V_{D D}=3 \mathrm{~V} \pm 10 \%, G N D=0 \mathrm{~V}$.
Table 2.

| Parameter | $+25^{\circ} \mathrm{C}$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: | :---: |
| ANALOG SWITCH <br> Analog Signal Range On Resistance (Ron) <br> On Resistance Match Between Channels ( $\Delta$ Ros) <br> On Resistance Flatness (Rflat(on) | 6 | $\begin{aligned} & 7 \\ & 10 \\ & \\ & 0.1 \\ & 0.4 \\ & 2.5 \\ & \hline \end{aligned}$ | $\begin{aligned} & 0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}} \\ & 12 \\ & 0.4 \end{aligned}$ | V <br> $\Omega$ typ <br> $\Omega$ max <br> $\Omega$ typ <br> $\Omega$ max <br> $\Omega$ typ | $\begin{aligned} & \mathrm{V}_{\mathrm{S}}=0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}} \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} ; \\ & \text { See Figure } 14 \\ & \mathrm{~V}_{\mathrm{S}}=0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}, \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{S}}=0 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}, \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} \end{aligned}$ |
| LEAKAGE CURRENTS <br> Source Off Leakage Is (Off) <br> Channel On Leakage Io, Is (On) | $\begin{aligned} & \pm 0.01 \\ & \pm 0.25 \\ & \pm 0.01 \\ & \pm 0.25 \end{aligned}$ | $\begin{aligned} & \pm 0.35 \\ & \pm 0.35 \end{aligned}$ | 5 | nA typ <br> nA max <br> nA typ <br> nA max | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{S}}=3 \mathrm{~V} / 1 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=1 \mathrm{~V} / 3 \mathrm{~V} ; \end{aligned}$ <br> See Figure 15 $V_{S}=V_{D}=1 \mathrm{~V} \text { or } \mathrm{V}_{\mathrm{S}}=\mathrm{V}_{\mathrm{D}}=3 \mathrm{~V} \text {; }$ <br> See Figure 16 |
| DIGITAL INPUTS Input High Voltage, $\mathrm{V}_{\mathrm{INH}}$ Input Low Voltage, VINL Input Current lind or $\mathrm{l}_{\mathrm{NH}}$ | 0.005 |  | $\begin{gathered} 2.0 \\ 0.8 \\ \\ \pm 0.1 \end{gathered}$ | $V$ min <br> $\checkmark$ max <br> $\mu \mathrm{A}$ typ <br> $\mu \mathrm{A} \max$ | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {INL }}$ or $\mathrm{V}_{\text {INH }}$ |
| DYNAMIC CHARACTERISTICS ${ }^{1}$ <br> ton <br> toff <br> Break-Before-Make Time Delay, $t_{D}$ <br> Off Isolation <br> Channel-to-Channel Crosstalk <br> Bandwidth -3 dB <br> $\mathrm{C}_{s}$ (Off) <br> $C_{d}, C_{s}(O n)$ | 10 <br> 4 <br> 8 $\begin{aligned} & -67 \\ & -87 \\ & -62 \\ & -82 \\ & 200 \\ & 7 \\ & 27 \end{aligned}$ |  | 15 | ns typ ns max ns typ ns max ns typ ns min dB typ dB typ <br> dB typ dB typ <br> MHz typ pF typ pF typ | $R \mathrm{~L}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ <br> $\mathrm{V}_{\mathrm{s}}=2 \mathrm{~V}$; See Figure 17 <br> $\mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ <br> $\mathrm{V}_{\mathrm{s}}=2 \mathrm{~V}$; See Figure 17 <br> $R_{L}=300 \Omega, C_{L}=35 \mathrm{pF}$ <br> $\mathrm{V}_{\mathrm{s} 1}=\mathrm{V}_{\mathrm{s} 2}=2 \mathrm{~V}$; See Figure 18 <br> $\mathrm{RL}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=10 \mathrm{MHz}$ <br> $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz}$; <br> See Figure 19 <br> $R_{L}=50 \Omega, C_{L}=5 \mathrm{pF}, \mathrm{f}=10 \mathrm{MHz}$ <br> $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz}$; <br> See Figure 20 <br> $R_{L}=50 \Omega, C_{L}=5 p F$; See Figure 21 |
| POWER REQUIREMENTS IDD | $\begin{aligned} & 0.001 \\ & 1.0 \end{aligned}$ |  |  | $\mu \mathrm{A}$ typ $\mu \mathrm{A}$ max | $\begin{aligned} & \mathrm{V} \mathrm{DD}=3.3 \mathrm{~V} \\ & \text { Digital inputs }=0 \mathrm{~V} \text { or } 3.3 \mathrm{~V} \end{aligned}$ |

[^1]
## ABSOLUTE MAXIMUM RATINGS

$\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, unless otherwise noted.
Table 3.

| Parameter | Rating |
| :--- | :--- |
| $V_{\text {DD }}$ to GND | $-0.3 \mathrm{~V} \mathrm{to}+7 \mathrm{~V}$ |
| Analog, Digital Inputs ${ }^{1}$ | -0.3 V to $\mathrm{VDD}+0.3 \mathrm{~V}$ or |
|  | 30 mA , whichever occurs |
| first |  |
| Peak Current, S or D | 100 mA |
|  | $($ Pulsed at $1 \mathrm{~ms}, 10 \%$ duty |
| Continuous Current, S or D | cycle max) |
| Operating Temperature Range | 30 mA |
| Storage Temperature Range | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ |
| Junction Temperature | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| MSOP Package, Power Dissipation | $150^{\circ} \mathrm{C}$ |
| ӨjA Thermal Impedance | 315 mW |
| $\theta_{\mathrm{JC}}$ Thermal Impedance | $206^{\circ} \mathrm{C} / \mathrm{W}$ |
| SOT-23 Package, Power Dissipation | $44^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\mathrm{JA}}$ Thermal Impedance | 282 mW |
| $\theta_{\mathrm{JC}}$ Thermal Impedance | $229.6^{\circ} \mathrm{C} / \mathrm{W}$ |
| Lead Soldering | $91.99^{\circ} \mathrm{C} / \mathrm{W}$ |
| Lead Temperature, Soldering | $300^{\circ} \mathrm{C}$ |
| (10 sec) |  |
| IR Reflow, Peak Temperature | $220^{\circ} \mathrm{C}$ |
| (<20 sec) |  |
| Soldering (Pb-Free) | $260(+0 /-5)^{\circ} \mathrm{C}$ |
| Reflow, Peak Temperature | 20 sec to 40 sec |
| Time at Peak Temperature | 1 kV |
| ESD |  |

[^2]Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one maximum rating may be applied at any one time.

## ESD CAUTION

|  | ESD (electrostatic discharge) sensitive device. <br> Charged devices and circuit boards can discharge <br> without detection. Although this product features <br> patented or proprietary protection circuitry, damage <br> may occur on devices subjected to high energy ESD. <br> Therefore, proper ESD precautions should be taken to <br> avoid performance degradation or loss of functionality. |
| :--- | :--- |

## ADG719

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



Figure 2. 6-Lead SOT-23


Figure 3. 8-Lead MSOP

Table 4. Pin description

| Pin Number |  |  |  |
| :--- | :--- | :--- | :--- |
| MSOP | SOT-23 | Mnemonic | Description |
| 1 | 5 | D | Drain Terminal. Can be used as an input or output. |
| 2 | 4 | S1 | Source Terminal. Can be used as an input or output. |
| 3 | 3 | GND | Ground (OV) Reference Pin. |
| 4 | 2 | VDD | Most Positive Power Supply Pin. |
| 5 | - | NC | Not Internally Connected. |
| 6 | 1 | IN | Digital Switch Control Pin. |
| 7 | - | NC | Not Internally Connected. |
| 8 | 6 | S2 | Source Terminal. Can be used as an input or output. |

Table 5. Truth Table

| ADG719 IN | Switch S1 | Switch S2 |
| :--- | :--- | :--- |
| 0 | ON | OFF |
| 1 | OFF | ON |

## TYPICAL PERFORMANCE CHARACTERISTICS



Figure 4. On Resistance vs. $V_{D}\left(V_{s}\right)$, Single Supplies


Figure 5. On Resistance vs. $V_{D}\left(V_{s}\right)$ for Different Temperatures, $V_{D D}=3 \mathrm{~V}$


Figure 6. On Resistance vs. $V_{D}\left(V_{S}\right)$ for Different Temperatures, $V_{D D}=5 \mathrm{~V}$


Figure 7. Leakage Currents vs. Temperature


Figure 8. Leakage Currents vs. Temperature


Figure 9. Supply Current vs. Input Switching Frequency


Figure 10. Off Isolation vs. Frequency


Figure 11. Crosstalk vs. Frequency


Figure 12. On Response vs. Frequency


Figure 13. Charge Injection vs. Source Voltage

## ADG719

## TEST CIRCUITS



Figure 15. Off Leakage


Figure 17. Switching Times


Figure 18. Break-Before-Make Time Delay, $t_{D}$

## ADG719



Figure 19. Off Isolation


CROSSTALK $=20$ LOG $\frac{\mathrm{V}_{\mathrm{OUT}}}{\mathrm{V}_{\mathrm{S}}}$ 峵
Figure 20. Channel-to-Channel Crosstalk


Figure 21. Bandwidth

## TERMINOLOGY

Ron
Ohmic Resistance between D and S.
$\Delta$ Ron
On Resistance Match between Any Two Channels
that is, Ron max - Ron min.
$\mathbf{R}_{\text {flat(on) }}$
Flatness is defined as the difference between the maximum and minimum value of on resistance, as measured over the specified analog signal range.

Is $_{\text {s }}$ (Off)
Source Leakage Current with the Switch Off.
$\mathrm{I}_{\mathrm{D}}, \mathrm{I}_{\mathrm{S}}(\mathbf{O n})$
Channel Leakage Current with the Switch On.
$\mathrm{V}_{\mathrm{D}}$ (Vs)
Analog Voltage on Terminals D and S.
Cs (Off)
Off Switch Source Capacitance.
$C_{\mathrm{D}}, \mathrm{C}_{\mathrm{s}}$ (On)
On Switch Capacitance.
ton
Delay between Applying the Digital Control Input and the Output Switching On.
toff
Delay between Applying the Digital Control Input and the Output Switching Off.
$t_{D}$
Off Time or On Time Measured between the 90\% Points of Both Switches, when Switching From One Address State to Another.

Crosstalk
A Measure of Unwanted Signal That Is Coupled through from One Channel to Another as a Result of Parasitic Capacitance.
Off Isolation
A Measure of Unwanted Signal Coupling through an Off Switch.

## Bandwidth

The Frequency at Which the Output is Attenuated by -3 dBs .
On Response
The Frequency Response of the On Switch.

## Insertion Loss

Loss due to On Resistance of Switch.

## APPLICATIONS INFORMATION

The ADG719 belongs to Analog Devices' new family of CMOS switches. This series of general-purpose switches has improved switching times, lower on resistance, higher bandwidths, low power consumption, and low leakage currents.

## ADG719 SUPPLY VOLTAGES

Functionality of the ADG719 extends from 1.8 V to 5.5 V single supply, which makes it ideal for battery-powered instruments where power efficiency and performance are important design parameters.
It is important to note that the supply voltage effects the input signal range, the on resistance, and the switching times of the part. By taking a look at the Typical Performance Characteristics and the Specifications, the effects of the power supplies can be clearly seen.

For $\mathrm{V}_{\mathrm{DD}}=1.8 \mathrm{~V}$ operation, Ron is typically $40 \Omega$ over the temperature range.

## ON RESPONSE VS. FREQUENCY

Figure 22 illustrates the parasitic components that affect the ac performance of CMOS switches (the switch is shown surrounded by a box). Additional external capacitances will further degrade some performance. These capacitances affect feedthrough, crosstalk, and system bandwidth.


Figure 22. Switch Represented by Equivalent Parasitic Components
The transfer function that describes the equivalent diagram of the switch (Figure 22) is of the form $\mathrm{A}(\mathrm{s})$ shown below:

$$
A(s)=R_{T}\left[\frac{s\left(R_{O N} C_{D S}\right)+1}{s\left(R_{T} R_{O N} C_{T}\right)+1}\right]
$$

where:

$$
\begin{aligned}
& \mathrm{R}_{\mathrm{T}}=\mathrm{R}_{\mathrm{LOAD}} /\left(\mathrm{R}_{\mathrm{LOAD}}+\mathrm{R}_{\mathrm{oN}}\right) \\
& \mathrm{C}_{\mathrm{T}}=\mathrm{C}_{\mathrm{LOAD}}+\mathrm{C}_{\mathrm{D}}+\mathrm{C}_{\mathrm{DS}}
\end{aligned}
$$

The signal transfer characteristic is dependent on the switch channel capacitance, $C_{D S}$. This capacitance creates a frequency zero in the numerator of the transfer function $A(s)$. Because the
switch on resistance is small, this zero usually occurs at high frequencies. The bandwidth is a function of the switch output capacitance combined with $C_{D S}$ and the load capacitance. The frequency pole corresponding to these capacitances appears in the denominator of $A(s)$.
The dominant effect of the output capacitance, $C_{D}$, causes the pole breakpoint frequency to occur first. Therefore, in order to maximize bandwidth, a switch must have a low input and output capacitance and low on resistance. The On Response vs. Frequency plot for the ADG719 can be seen in Figure 12.

## OFF ISOLATION

Off isolation is a measure of the input signal coupled through an off switch to the switch output. The capacitance, $C_{D S}$, couples the input signal to the output load when the switch is off, as shown in Figure 23.


Figure 23. Off Isolation Is Affected by External Load Resistance and Capacitance

The larger the value of $C_{D S}$, the larger the values of feedthrough that will be produced. Figure 10 illustrates the drop in off isolation as a function of frequency. From dc to roughly 200 kHz , the switch shows better than -95 dB isolation. Up to frequencies of 10 MHz , the off isolation remains better than -67 dB . As the frequency increases, more and more of the input signal is coupled through to the output. Off isolation can be maximized by choosing a switch with the smallest $C_{D S}$ possible. The values of load resistance and capacitance also affect off isolation, since they contribute to the coefficients of the poles and zeros in the transfer function of the switch when open.

$$
A(s)=\left[\frac{s\left(R_{L O A D} C_{D S}\right)}{s\left(R_{L O A D}\right)\left(C_{L O A D}+C_{D}+C_{D S}\right)+1}\right]
$$

## OUTLINE DIMENSIONS



Figure 24. 8-Lead Mini Small Outline Package [MSOP] (RM-8)
Dimensions shown in millimeters


COMPLIANT TO JEDEC STANDARDS MO-178-AB
Figure 25. 6-Lead Small Outline Transistor Package [SOT-23] (RJ-6)
Dimensions shown in millimeters

## ADG719

ORDERING GUIDE

| Model $^{1}$ | Temperature Range | Package Description | Package Option | Branding |
| :--- | :--- | :--- | :--- | :--- |
| ADG719BRM | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | -Lead MSOP | RM-8 | S5B |
| ADG719BRM-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 -Lead MSOP | RM-8 | S5B |
| ADG719BRM-REEL7 | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 -Lead MSOP | RM-8 | S5B |
| ADG719BRMZ | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 -Lead MSOP | RM-8 | S5B\# |
| ADG719BRMZ-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 -Lead MSOP | RM-8 | S5B\# |
| ADG719BRMZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 -Lead MSOP | RM-8 | S5B |
| ADG719BRT-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 6 -Lead SOT-23 | RJ-6 | S5B |
| ADG719BRT-REEL7 | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | R-Lead SOT-23 | S5B |  |
| ADG719BRT -500RL7 | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 6-Lead SOT-23 | RJ-6 | S5B\# |
| ADG719BRTZ -500RL7 | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 6 -Lead SOT-23 | RJ-6 | S5B\# |
| ADG719BRTZ-R2 | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 6-Lead SOT-23 | RJ-6 | S5B\# |
| ADG719BRTZ-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 6-Lead SOT-23 | RJ-6 |  |
| ADG719BRTZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 6-Lead SOT-23 |  |  |

[^3]| ADG719 |
| :--- |

NOTES

## ADG719

## NOTES

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for Analog Switch ICs category:
Click to view products by Analog Devices manufacturer:
Other Similar products are found below :
DG9233EDY-GE3 NLAS4684FCTCG NLAS5223BLMNR2G NLV74HC4066ADR2G MC74HC4067ADTG NLX2G66DMUTCG
NS5A4684SMNTAG 732480R 733995E 425541DB 425528R 099044FB FSA221UMX MAX4888ETI+T MAX4968CEXB+ MAX4760EWX+T NLAS3799BMNR2G NLAS5123MNR2G NLAS5213AMUTAG NLAS7222AMTR2G MAX14807ECB+ MAX4968ECM + NLV14066BDG LC78615E-01US-H PI5A4599BCEX PI5A3157BZUEX ADG613SRUZ-EP NLAS4717EPFCT1G PI5A3167CCEX MAX4744ELB+T MAX4802ACXZ+ DG4051EEN-T1-GE4 SLAS3158MNR2G PI5A3157BC6EX PI5A392AQE MAX4744HELB+T PI5A4157ZUEX MC74HC4067ADTR2G PI5A4158ZAEX PI5A3166TAEX MAX4901EBL+T MAX14510EEVB+T PI3A3899ZTEX MAX4996ETG+T MAX4889AETO+T MAX14508EEVB+T MAX4701ETE+T MAX4996LETG+T NLX2G66FCTAG HI1-5051-2


[^0]:    ${ }^{1}$ Guaranteed by design, not subject to production test.

[^1]:    ${ }^{1}$ Guaranteed by design, not subject to production test.

[^2]:    ${ }^{1}$ Overvoltages at $\mathrm{IN}, \mathrm{S}$, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given

[^3]:    ${ }^{1} Z=$ RoHS Compliant Part.

